

Two-dimensional Obstructed Atomic Insulators with Fractional Corner Charge in MA_2Z_4 Family

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According to topological quantum chemistry, a class of electronic materials have been called obstructed atomic insulators (OAI), in which a portion of valence electrons necessarily have their centers located on some empty *Wyckoff* positions without atoms occupation in the lattice. The obstruction of centering these electrons coinciding with their host atoms is nontrivial and results in metallic boundary states when the boundary is properly cut. Here, on basis of first-principles calculations in combination with topological quantum chemistry analysis, we propose two dimensional MA_2Z_4 ($\text{M} = \text{Cr}, \text{Mo}$ and W ; $\text{A} = \text{Si}$ and Ge , $\text{Z} = \text{N}, \text{P}$ and As) monolayer family are all OAIs. A typical case is the recently synthesized MoSi_2N_4 . Although it is a topological trivial insulator with the occupied electronic states being integer combination of elementary band representations, it has valence electrons centering empty *Wyckoff* positions. It exhibits unique OAI-induced metallic edge states along the $(1\bar{1}0)$ edge of MoSi_2N_4 monolayer and the in-gap corner states at three vertices of certain hexagonal nanodisk samples respecting C_3 rotation symmetry. The readily synthesized MoSi_2N_4 is quite stable and has a large bulk band gap of 1.94 eV, which makes the identification of these edge and corner states most possible for experimental clarification.

Introduction. –Topological materials including topological insulators and topological semimetals have attracted intensive attentions^{1–31}, mainly due to their nontrivial bulk band dispersion and metallic surface (or edge) states. In recent years, the development of topological quantum chemistry (TQC)^{32–34} and symmetry indicator^{35,36} provides convenient and efficient tools to the high-throughput discoveries of topological quantum materials^{37–41}. Within the TQC theory, topological trivial insulators can be defined by band representations (BRs) of valence bands, which are equivalent to a set of exponentially localized Wannier functions⁴². Any BRs can be given by a linear combination of elementary band representations (EBRs), which are induced from irreducible representations at maximal *Wyckoff* positions (WPs)^{42–44}. If some of the coefficients of linear combination of elementary band representations (LCEBRs) are rational fractions, the material is a stable topological insulator or topological semimetal. If all the LCEBRs of a material exhibit non-negative integer coefficients, the materials is then a topological trivial insulator⁴⁵.

Recently, a series of unique topologically trivial insulators, dubbed obstructed atomic insulators (OAIs), have been found^{45,46}. In difference from the BRs of atomic insulators induced from the atomic orbitals locating at atom-occupied *Wyckoff* positions (AOWPs), the BRs of OAIs are induced from additional atom-unoccupied *Wyckoff* positions (AUWPs). In other words, for atomic insulators electrons fill atomic orbitals at the AOWPs, but for OAIs a portion of electrons have to occupy those at the AUWPs. Note that in any periodic lattice of solid materials there are many so-called AUWPs, which can be easily identified via the international tables for crystallography. Nevertheless, not all AUWPs are

necessary for OAIs, while only those electron-filled AUWPs are necessary for OAIs. Such electron-filled AUWPs for OAIs are also named as obstructed Wannier charge centers (OWCCs)⁴⁵. Importantly, when the cleavage termination cuts through those electron-filled AUWPs (namely, OWCCs) in an OAI, the metallic surface states will emerge. This crucial feature makes OAIs be potential candidates for superconductivity and catalysis^{46–50}. To date, OAIs including 3,383 paramagnetic and 30 magnetic materials are reported in three-dimensional (3D) materials^{45,46}. However, 2D OAIs, which could be used in low dimensional devices^{51,52}, have not been systematically investigated.

Recently, 2D monolayer MA_2Z_4 family^{53,54} with septuple-atomic-layer lattices have been experimentally or theoretically reported. This MA_2Z_4 family crystallizes in five different crystalline phases, including 72 theoretically suggested stable materials⁵⁴. By inspecting the electronic structure of theoretically predicted stable monolayer $\alpha_1\text{-WSn}_2\text{N}_4$ semiconductor with an indirect band gap of 0.18 eV, we found that it possesses the typical inverted energy band between $\text{W-}d_{z^2}$ and $\text{N-}p_z$ orbitals at the centered Γ point of the Brillouin Zone (BZ) around the band gap (Appendix Fig. A1). Although the band inversion typically signals to have nontrivial topological nature, both its topological indicator and mirror chern number equal to zero, indicating a topological trivial insulator. Furthermore, by deriving its electronic band structure of the edge boundary, metallic edge states nevertheless occur, which is very similar to the metallic surface states of 3D OAIs^{45,46}. Interestingly, we further revealed that in total 16 monolayer MA_2Z_4 semiconductors with 34 valence electrons (VEC) including experimentally synthesized $\alpha_1\text{-MoSi}_2\text{N}_4$ exhibit sim-

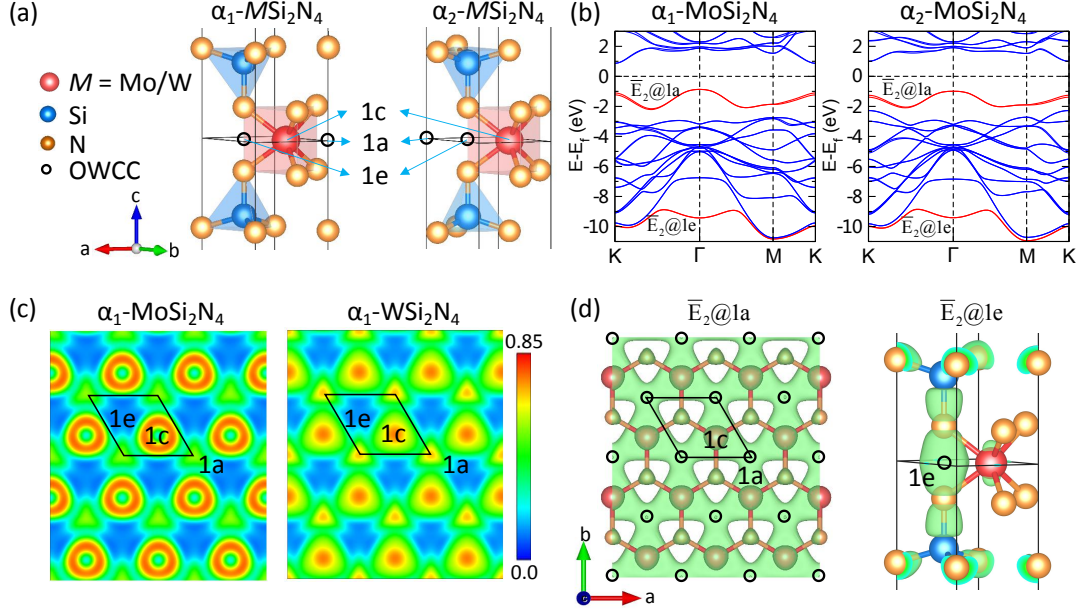


FIG. 1. (Color online) Lattice and electronic structures of MSi_2N_4 monolayer ($M = \text{Mo, W}$). (a) Lattice structures of α_1 - and α_2 - MSi_2N_4 monolayer, where the black circle denotes the obstructed wannier charge center (OWCC). (b) The electronic band structures of α_1 - and α_2 - $MoSi_2N_4$ monolayer with the inclusion of spin-orbit coupling, where the red bands correspond to the band representation of $\bar{E}_2@1a$ and $\bar{E}_2@1e$. (c) The electron localization functions (ELF) of α_1 - $MoSi_2N_4$ and α_1 - WSi_2N_4 monolayer. $1a$, $1c$, and $1e$ are Wyckoff positions, and the localized charges occupy at the $1a$ and $1c$ Wyckoff positions. The solid lines denote the primitive cell of α_1 - MSi_2N_4 monolayer materials. (d) The charges distribution of the band representation $\bar{E}_2@1a$ and $\bar{E}_2@1e$ of α_1 - $MoSi_2N_4$. The green hook face is the isosurface with value of $0.008 \text{ e}/\text{\AA}^3$ and the black circles denote the OWCCs at both $1a$ and $1e$. In the left panel of (d), to show $1a$ position clearly, the top and bottom Si-N layers of α_1 - $MoSi_2N_4$ monolayer are removed.

ilar electronic band features to α_1 - WSn_2N_4 and they all are topological trivial insulators. Their special electronic structures make us think over whether these monolayer MA_2Z_4 semiconductors are 2D OAI. If yes, any novel properties will emerge in these 2D OAI family?

With this motivation, by means of first-principles calculations in combination with TQC analysis, we report 16 monolayer 34-VEC MA_2Z_4 semiconductors as 2D OAIs. By taking the experimentally synthesized $MoSi_2N_4$ semiconductor as a typical example, we identify the occurrence of the localized charge at the AUWPs as the crucial fingerprint of OAIs. Additionally, the metallic edge states appear in the band gap along the $(1\bar{1}0)$ direction on the boundary of $MoSi_2N_4$ monolayer at which cleavage terminations exactly cut through OWCCs. Interestingly, in-gap corner states found in second-order topological insulators also occur in the C_3 -symmetric hexagonal nanodisk of $MoSi_2N_4$.

Lattice structure of $MoSi_2N_4$ monolayer. — The experimentally synthesized α_1 - $MoSi_2N_4$ ⁵³ with 34 VEC belongs to MA_2Z_4 family⁵⁴. In our theoretical predictions⁵⁴, there are 15 monolayer 34-VEC MA_2Z_4 semiconductors, which mainly crystallize in two classes of lattice structures, α_1 - and α_2 - MA_2Z_4 . For $MoSi_2N_4$, the formation energy of α_1 - $MoSi_2N_4$ is 24 meV/atom lower than that of α_2 - $MoSi_2N_4$. Similarly, α_1 phase of WSn_2N_4 is energetically more stable by 1.3 meV/atom than its α_2 phase. Both α_1 - and α_2 - $MoSi_2N_4$

have the hexagonal lattices with the atomic sequence of N-Si-N-Mo-N-Si-N (the space group of $P\bar{6}m2$ (No. 187)²), as shown in Fig. 1(a). This septuple-atom-layer can be viewed by inserting 2H- MoS_2 -type MoN_2 into α -InSe-type SiN. In α_1 - $MoSi_2N_4$ there are two different nitrogen WPs of $2g$ ($0, 0, \pm z$) and $2i$ ($2/3, 1/3, \pm z$), whereas for α_2 - $MoSi_2N_4$ two different nitrogen WPs of $2h$ ($1/3, 2/3, \pm z$) and $2i$ ($2/3, 1/3, \pm z$). Thus, here we denote three different nitrogen WPs as N_g , N_i , and N_h for sake of convenient discussion below. As illustrated in Fig. 1(a), both N_g for α_1 - $MoSi_2N_4$ and N_h for α_2 - $MoSi_2N_4$ locate at the top or the bottom of the monolayer $MoSi_2N_4$, but N_i atoms sit in the layer between Si of $2i$ ($2/3, 1/3, \pm z$) and Mo of $1c$ ($1/3, 2/3, 0$). Thus, nitrogen atoms form two basic local structures, a tetrahedron consisting of three N_g (or N_h) atoms and one N_i atom, and a triangular prism composed of six N_i atoms. Si and Mo atoms sit at the centering positions of the tetrahedron and the prism, respectively. It needs to be emphasized that N_i and Si atoms have the same Wyckoff notations of $2i$ ($2/3, 1/3, \pm z$) but with different z values.

OAI identification of $MoSi_2N_4$ monolayer. — α_1 - $MoSi_2N_4$ is an indirect semiconductor with an experimental band gap of 1.94 eV, comparable to the DFT-derived gap of 1.74 eV (PBE) and 2.30 eV (HSE06)⁵⁴. It is also a topologically trivial insulator, according to topological analysis using mirror chern number. Conceptually, the occupied electronic bands

TABLE I. All possible decompositions of the BRs of α_1 -MoSi₂N₄ and α_2 -MoSi₂N₄ into linear combinations of the EBRs in the double space group P6m2 (No. 187). The first row gives the possible EBRs induced from different orbitals at the *Wyckoff* positions 1*a*, 1*c*, and 1*e*; the numbers below are the multiplicities of each EBR in the corresponding decomposition. Note that only a portion of LCEBRs are listed here and the complete LCEBRs are given in the Appendix Table A1 and Table A2.

Compounds	$\bar{E}_1@1a$	$\bar{E}_2@1a$	$\bar{E}_3@1a$	$\bar{E}_1@1c$	$\bar{E}_2@1c$	$\bar{E}_3@1c$	$\bar{E}_1@1e$	$\bar{E}_2@1e$	$\bar{E}_3@1e$
α_1 -MoSi ₂ N ₄	6	7	5	1	0	0	1	1	0
	5	6	4	2	1	1	1	1	0
	4	5	3	3	2	2	1	1	0
	3	4	2	4	3	3	1	1	0
	2	3	1	5	4	4	1	1	0
	1	2	0	6	5	5	1	1	0
α_2 -MoSi ₂ N ₄	5	6	5	2	1	0	1	1	0
	4	5	4	3	2	1	1	1	0
	3	4	3	4	3	2	1	1	0
	2	3	2	5	4	3	1	1	0
	1	2	1	6	5	4	1	1	0
	0	1	0	7	6	5	1	1	0

of 3D topological trivial insulator can be expressed by a non-negative integer linear combination of EBRs using the TQC theory^{32–34}. Since MoSi₂N₄ monolayer is a 2D material, only the band representations (BRs) of high symmetry points Γ , M and K at $k_z=0$ plane are considered. And since the EBRs of *Wyckoff* positions 2*g*, 2*h* and 2*i* can be obtained by the combinations of EBRs of *Wyckoff* positions 1*a*, 1*c*, and 1*e*, the maximum *Wyckoff* positions 1*a*, 1*c*, and 1*e* are chosen to perform the EBRs decomposition. Therefore, the LCEBRs of the occupied electronic bands of α_1 - and α_2 -MoSi₂N₄ have been derived in Table I. Note that we only listed a portion of LCEBRs, and the complete LCEBRs of α_1 - and α_2 -MoSi₂N₄ can be found in Appendix Table A1 and Table A2, respectively. Interestingly, for α_1 -MoSi₂N₄, the results of all the LCEBRs show that there are six EBRs ($\bar{E}_1@1a$, $\bar{E}_2@1a$, $\bar{E}_1@1c$, $\bar{E}_2@1c$, $\bar{E}_1@1e$ and $\bar{E}_2@1e$) with the non-zero integer combination. This fact means these six EBRs can not be decomposed and they have to be linked to electron-filled *Wyckoff* positions of 1*a*, 1*c*, and 1*e*. The 1*c* site is occupied by Mo atom whereas the 1*a* and 1*e* sites are *null* without any atomic occupation. In terms of the OAI definition^{45,46}, α_1 -MoSi₂N₄ is an OAI and the 1*a* and 1*e* sites are the OWCC. Similarly, the non-zero integer of LCEBR of the 1*a* and 1*e* AUWPs indicates that α_2 -MoSi₂N₄ is also an OAI, and the 1*a* and 1*e* AUWPs are the OWCC.

For the OAI feature, the most key point is to check whether the AUWPs have the localized charges (namely, electron filling). To elucidate the real-space charge localizations of MoSi₂N₄ we have thus visualized the electron localization function (ELF) (Fig. 1(c)) on the centering Mo-atom layer in which four indecomposable EBRs correspond to both 1*a* (*null*) and 1*c* (Mo) AUWP. It can be seen that the charges obviously localize at the 1*c* Mo site and the *null* 1*a* AUWP. The feature is more apparent in α_1 -WSi₂N₄ and α_2 -MoSi₂N₄ (see Appendix Fig. A2). We find that the localized charges at the 1*c* AUWP are mainly contributed by Mo atoms, whereas the ones at the *null* 1*a* AUWP originate from the orbital hybridizations between Mo and N_{*i*} atoms, which is in good agreement

with obstructed atomic limit for SSH model with *sp* orbital hybridization³². Furthermore, in Fig. 1(d) we plot the partial charge densities of the two indecomposable EBRs responsible for the isolated electronic bands marked by $\bar{E}_2@1a$ and $\bar{E}_2@1e$ in Fig. 1(b), evidencing the distribution of charges at both the 1*a* and 1*e* AUWPs.

Following the similar analysis, we have checked another 15 MA₂Z₄ monolayer semiconductors with 34 valence electrons predicted in our previous work⁵⁴. The results demonstrate that all of them are typical OAIs, as summarized in Appendix Table A3.

Obstructed metallic edge states and in-gap corner states.

— Physically, topological nontrivial materials with *d*-1 dimensional boundary states are defined as first-order topological materials (where *d* is the dimension of topological materials). The ones with *d*-*n* (*n* > 1) dimensional boundary states are the *n*th order topological materials. Interestingly, In similarity with 3D topological insulators, for a 3D OAI the *d*-1 dimensional metallic surface states occur on the 2D surface with the cleavage terminations exactly cutting through an OWCC^{45,46}. Hence, it is desirable to examine to see whether or not the metallic edge states of the 1D boundary occur for the 2D OAI of monolayer MoSi₂N₄.

Note that because for α_1 -MoSi₂N₄ its two N_{*g*} and two N_{*i*} atoms are exactly above its OWCC-type 1*a* (0, 0, 0) and 1*e* (2/3, 1/3, 0) AUWPs, it is hard to cut an edge that only contains the OWCC but without containing the N atoms. However, this difficulty does not occur in its α_2 phase of OAI, since no atoms are exactly above its OWCC-type 1*a* AUWP (see Fig. 1(a) and Table I). On basis of Wannier-based Hamiltonian of α_2 -MoSi₂N₄, we derived the electronic band structures of the edge boundary along (1 $\bar{1}$ 0) direction, which only cuts through the OWCC-type 1*a* (0, 0, 0) AUWP (Fig. 2(a-c)). Notably, the apparent obstructed metallic edge states (OESs) occur between the conduction bands (CB) and valence bands (VB) of α_2 -MoSi₂N₄ monolayer. This phenomenon agrees well with the observations in 3D OAIs^{45,46}. By calculating the charge distribution of the OESs at the Fermi level within a

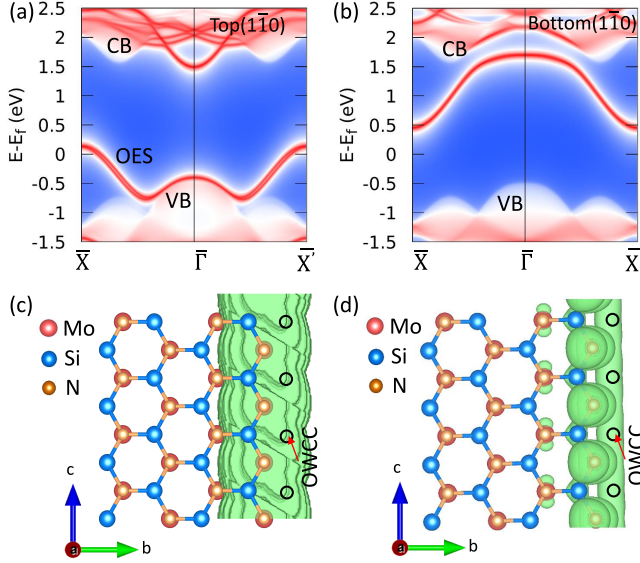


FIG. 2. (Color online) Obstructed metallic edge states of α_2 - MoSi_2N_4 monolayer. (a-b) The projected edge states along the (110) direction of the boundary with cutting through the OWCC at 1a site. CB and VB are the conduction bands and valence bands. OES is the obstructed metallic edge states. (c) Charge distributions of metallic OES at Fermi level shown in (a) derived by Wannier-based Hamiltonian of α_2 - MoSi_2N_4 nanoribbon. (d) Charge distributions of metallic OES at Fermi level shown in (a) derived by first-principles calculations of α_2 - MoSi_2N_4 nanoribbon. The black circle marked by red arrow are OWCC. Green hook face is the isosurface of the charge of OES with a value of $0.002 \text{ e}/\text{\AA}^3$.

nanowire model with a width of 20 unit cells, the charges localize around the OWCC-type $1a$ AUWP and the decay of the OESs only has a depth of about 0.4 nm, as seen in Fig. 2(c). Such result is also verified by the first-principles calculations, in Fig. 2(d).

Next we turn to checking whether or not the 2D OAI of monolayer MoSi_2N_4 has the $d-2$ dimensional (namely zero-dimensional (0D)) in-gap corner states. We derived the electronic structures of the 0D nanodisk modeling of α_1 - MoSi_2N_4 . By analyzing its structural details (see Appendix Fig. A3, Fig. A4, and Table A4), we constructed a C_3 -symmetric triangle and hexagonal nanodisk with the armchair edge to keep the electrically neutral stoichiometric ratio of 1:2:4 over Mo:Si:N. Since monolayer MoSi_2N_4 holds three types of maximum *Wyckoff* positions, there are three possible geometries for both triangle and hexagonal nanodisks by varying the type of atom at center site. No matter which type of atom sits at the center of the C_3 -symmetric triangle or hexagonal nanodisk, their stoichiometric ratio is always remained by removing the center atoms (see Appendix Table A4).

To argue whether the monolayer MoSi_2N_4 holds the in-gap corner states, one has to see the so-called gapped edge states on the boundaries and the in-gap corner states siting the vertexes of the C_3 -symmetric triangle or hexagonal nanodisk. However, depending on the *filling anomaly* at the center

site, the in-gap corner states certainly occur in C_3 -symmetric triangle and hexagonal nanodisk.

Recently, a general formula to calculate the corner charges of the C_n symmetry nanodisk was developed⁵⁵⁻⁵⁷, as follows,

$$Q_{\text{corner}} = Q_{c-X}^{(n)} \equiv \frac{(n_X^{(\text{ion})} - n_X^{(e)}) |e|}{n} \pmod{|e|}, \quad (1)$$

where $Q_{c-X}^{(n)}$ means the corner charge when the center of the crystal locates at the X site, n is the fold of rotation axis. $n_X^{(\text{ion})}|e|$ and $n_X^{(e)}$ are the ionic charges and the number of electronic Wannier functions at the X site, respectively. Applying Eq. 1 to monolayer MoSi_2N_4 , we obtained the corner charge of the C_3 -symmetric triangle or hexagonal nanodisk of $Q_{1a}^{(n)} = 1/3 |e|$, $Q_{1e}^{(n)} = 2/3 |e|$ and $Q_{1c}^{(n)} = 0 |e|$. Here, the $1a$, $1e$ and $1c$ sites are responsible for the N, Si and Mo atoms at the center of the C_3 -symmetric crystals. Furthermore, we derived the energy spectra and charge distributions of our constructed triangle or hexagonal nanodisk. Note that the energy spectra and charge distribution of the N-centered hexagonal nanodisk are further compiled in Fig. 3(a, d), while the others are given in Appendix Fig. A5. It can be seen that three corner states at the N atoms meeting the C_3 rotational symmetry are in-gap and nearly zero-energy, labeling Nos. 718, 719 and 720. The other three corners without any charge distribution can be actually viewed as charge neutral "edges". The states of Nos. 718 and 719 are occupied and the No. 720 states are unoccupied. Because this system is spinless and the number of electrons of this system is 1438, we need to add two or subtract four electrons to make this system fully occupied or fully empty so that the system is gapped. The added two or subtracted four electrons correspond to $-2/3 |e|$ and $4/3 |e|$ corner charge at its each C_3 -symmetry corner. This result is equivalent to the calculated $1/3 |e|$ through Eq. 1. We note that the same conditions exist in the corner charge calculations of both Si-centered and Mo-centered hexagonal nanodisks. In Si-centered hexagonal nanodisk, three corner states are separated by one edge state (see Figs. 3(b, e) and Appendix Fig. A6). The corner state below edge state can be pushed into the gap of edge via an appropriate edge potential³². In Mo-centered hexagonal nanodisk, the states near the Fermi level are distributed not only at three corners in similarity to those of N-centered hexagonal nanodisk, but also at three charge neutral "edges". Therefore, no corner states occur in their energy level near the Fermi level, which reflects well the zero corner charge of the Mo-centered hexagonal nanodisk (see Figs. 3(c, f) and Appendix Fig. A7).

Conclusions. — To summarize, we have identified the 16 MA_2Z_4 monolayer family materials with 34 valence electrons as 2D obstructed atomic insulators. They are featured by the occurrence of half-filled obstructed metallic edge states in 1D nanowires and in-gap corner states in 0D C_3 -symmetric hexagonal nanodisks. Moreover, the 2H- MoS_2 monolayer and α - InSe monolayer, the two basic constituent units for the MA_2Z_4 monolayer family, are also identified as obstructed atomic insulators. Our work proposes a promising realization of 2D obstructed atomic insulators without inversion symmetry and provides a new platform to explore exotic phases of condensed matter and their associated novel properties.

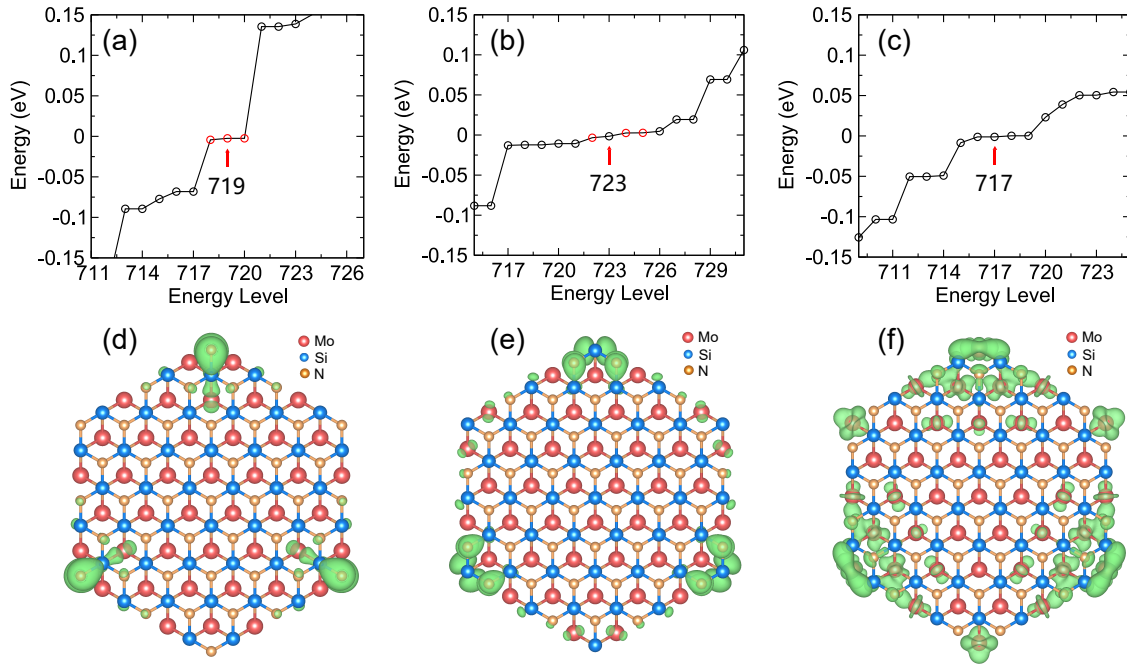


FIG. 3. (Color online) (a-c) Energy spectra of C_3 -symmetric hexagonal-shaped nanodisk of α_1 - MoSi_2N_4 with the N, Si, and Mo atom in the center, where the occupied energy level is marked by the red arrow and red circles represent corner states. (d-f) The charge distributions of the 718, 722, and 716 energy levels appearing in (a)-(c), respectively.

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Appendix A: Computational methods

Vienna ab *initio* simulation package (VASP)^{58,59} with exchange-correlation potential of Perdew-Burke-Ernzerhof (PBE) and projector augmented wave (PAW) method was used to perform first-principles calculations. 20 Å vacuum was set to exclude the interactions between the layers with periodic images. 500 eV cutoff energy and $15 \times 15 \times 1$ k -mesh in Γ -centered Monkhorst-Pack scheme were chosen in self-consistent calculation process. The structure was optimized until the force and energy less than 10^{-3} eV/Å and 10^{-6} eV/Å, respectively. All the C_3 -symmetric nanodisks were calculated by only Γ points. In addition, combating with Wannier90⁶² code, density functional theory (DFT)-derived Wannier functions (WFs) was constructed. And the Hamiltonians for each compounds were derived. Iterative Green functions method⁶¹ was applied to calculate the semi-infinite spectral function.

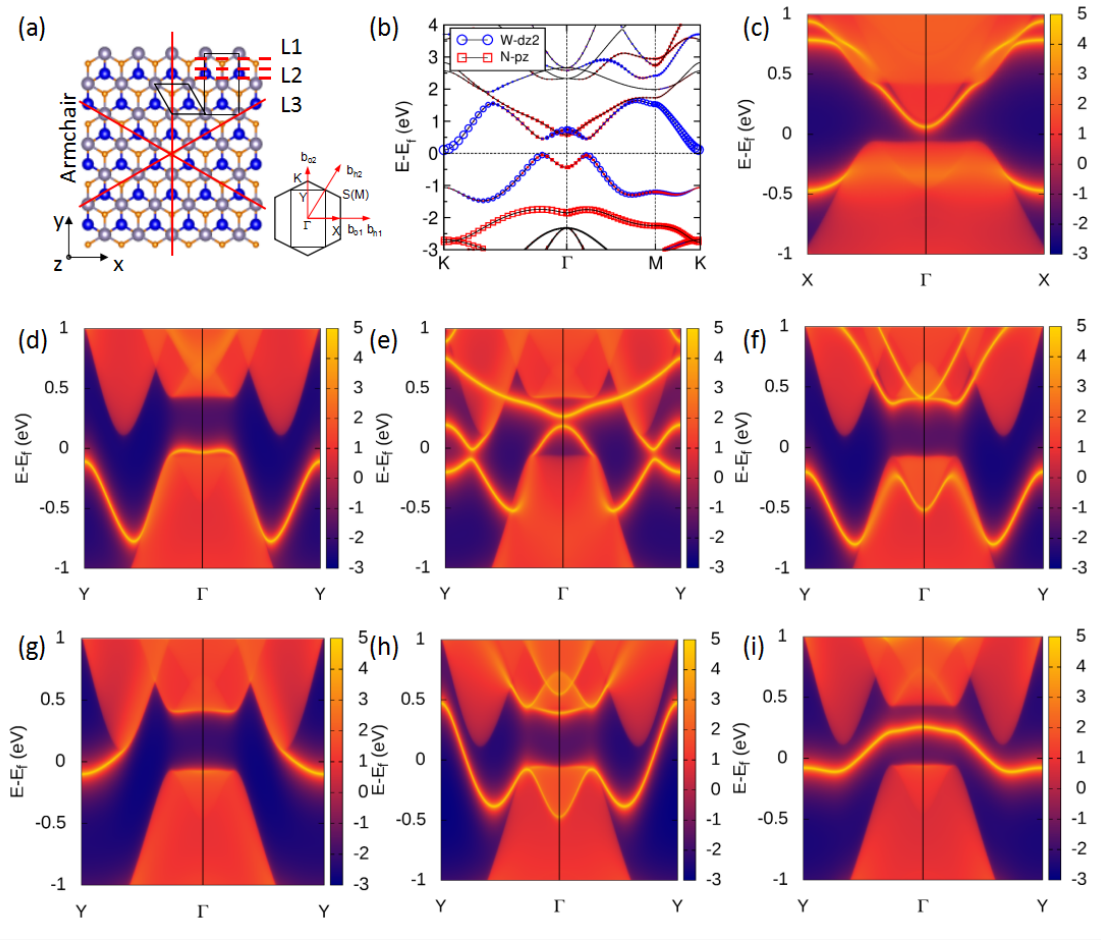


FIG. A1. (a) The top view of constructed orthorhombic cell of α_2 - WSn_2N_4 . The armchair edge is paralleled to mirror M_x . $L1_{up}$ and $L1_{down}$ ($i=1, 2, 3$) are the edge above or below line L_i . The insert shows the Brillouin zone of orthorhombic and hexagonal cell. (b) The band structure of α_2 - WSn_2N_4 . The blue circles and red square are the weight of W_{dz^2} and N_{pz} . The spectral function for (c) armchair, (d) $L1_{up}$, (e) $L1_{down}$, (f) $L2_{up}$, (g) $L2_{down}$, (h) $L3_{up}$ and (i) $L3_{down}$ edges. The bright gold, red and navy part represent surface states, bulk states and vacuum, respectively.

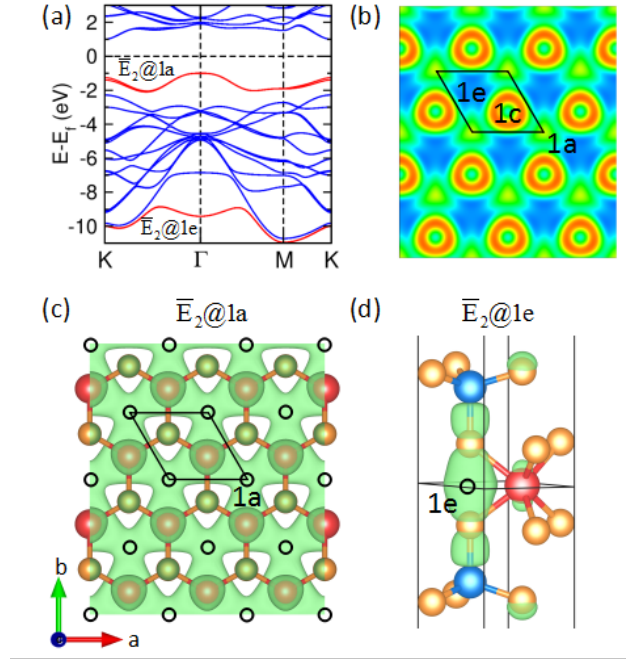


FIG. A2. Electronic structure of α_2 -MoSi₂N₄ monolayer. (a) The band structure of α_2 -MoSi₂N₄ monolayer, where the red bands correspond to the band representation of $\bar{E}_2@1a$ and $\bar{E}_2@1e$. (b) The ELF of α_2 -MoSi₂N₄ monolayer. $1a$, $1c$, and $1e$ are *Wyckoff* sites, and charges localize at *Wyckoff* sites $1a$ and $1c$. The diamond solid line are the primitive cell of α_2 -MoSi₂N₄ monolayer. The charges distribution of band representation $\bar{E}_2@1a$ (c) and $\bar{E}_2@1e$ (d) of α_2 -MoSi₂N₄. The green hook face is the isosurface with value of 0.008. The black circles are OWCCs at $1a$ and $1e$.

TABLE A1. All possible decompositions of the BR of α_1 -MoSi₂N₄ into linear combination of the EBRs in double space group $P\bar{6}m2$ (No. 187). The first column gives the EBRs induced from different orbitals at *Wyckoff* positions $1a$, $1c$, and $1e$; the numbers below are the multiplicities of each EBR in the corresponding decomposition.

No.	$\bar{E}_1@1c$	$\bar{E}_2@1c$	$\bar{E}_3@1c$	$\bar{E}_1@1a$	$\bar{E}_2@1a$	$\bar{E}_3@1a$	$\bar{E}_1@1e$	$\bar{E}_2@1e$	$\bar{E}_3@1e$
#01	6	7	5	1	0	0	1	1	0
#02	5	6	4	2	1	1	1	1	0
#03	4	5	3	3	2	2	1	1	0
#04	3	4	2	4	3	3	1	1	0
#05	2	3	1	5	4	4	1	1	0
#06	1	2	0	6	5	5	1	1	0
#07	5	6	4	1	0	0	2	2	0
#08	4	5	3	2	1	1	2	2	1
#09	3	4	2	3	2	2	2	2	1
#10	2	3	1	4	3	3	2	2	1
#11	1	2	0	5	4	4	2	2	1
#12	4	5	3	1	0	0	3	3	2
#13	3	4	2	2	1	1	3	3	2
#14	2	3	1	3	2	2	3	3	2
#15	1	2	0	4	3	3	3	3	2
#16	3	4	2	1	0	0	4	4	3
#17	2	3	1	2	1	1	4	4	3
#18	1	2	0	3	2	2	4	4	3
#19	2	3	1	1	0	0	5	5	4
#20	1	2	0	2	1	1	5	5	4
#21	1	2	0	1	0	0	6	6	5

TABLE A2. All possible decompositions of the BR of α_2 -MoSi₂N₄ into linear combination of the EBRs in double space group $\bar{P}6m2$ (No. 187). The first column gives the EBRs induced from different orbitals at Wyckoff positions 1a, 1c, and 1e; the numbers below are the multiplicities of each EBR in the corresponding decomposition.

No.	$\bar{E}_1@1c$	$\bar{E}_2@1c$	$\bar{E}_3@1c$	$\bar{E}_1@1a$	$\bar{E}_2@1a$	$\bar{E}_3@1a$	$\bar{E}_1@1e$	$\bar{E}_2@1e$	$\bar{E}_3@1e$
#01	5	6	5	2	1	0	1	1	0
#02	4	5	4	3	2	1	1	1	0
#03	3	4	3	4	3	2	1	1	0
#04	2	3	2	5	4	3	1	1	0
#05	1	2	1	6	5	4	1	1	0
#06	0	1	0	7	6	5	1	1	0
#07	4	5	4	2	1	0	2	2	0
#08	3	4	3	3	2	1	2	2	1
#09	2	3	2	4	3	2	2	2	1
#10	1	2	1	5	4	3	2	2	1
#11	0	1	0	6	5	4	2	2	1
#12	3	4	3	2	1	0	3	3	2
#13	2	3	2	3	2	1	3	3	2
#14	1	2	1	4	3	2	3	3	2
#15	0	1	0	5	4	3	3	3	2
#16	2	3	2	2	1	0	4	4	3
#17	1	2	1	3	2	1	4	4	3
#18	0	1	0	4	3	2	4	4	3
#19	1	2	1	2	1	0	5	5	4
#20	0	1	0	3	2	1	5	5	4
#21	0	1	0	2	1	0	6	6	5

TABLE A3. Summary of OAI features of 17 34-VEC MA₂Z₄ materials, 2H-MoS₂, and α -InSe .

No.	compounds name	phase type	OAI or not	OWCC
01	CrSi ₂ N ₄	α_1	Y	1a,1e
02	MoSi ₂ N ₄	α_1	Y	1a,1e
03	MoSi ₂ N ₄	α_2	Y	1a,1e
04	WSi ₂ N ₄	α_1	Y	1a,1e
05	MoGe ₂ N ₄	α_1	Y	1a
06	WGe ₂ N ₄	α_1	Y	1a
07	CrSi ₂ P ₄	α_2	Y	1a,1e
08	MoSi ₂ P ₄	α_2	Y	1a,1e
09	WSi ₂ P ₄	α_2	Y	1a,1e
10	CrGe ₂ P ₄	α_2	Y	1a
11	MoGe ₂ P ₄	α_2	Y	1a
12	WGe ₂ P ₄	α_2	Y	1a
13	MoSi ₂ As ₄	α_2	Y	1a,1e
14	WSi ₂ As ₄	α_2	Y	1a,1e
15	MoGe ₂ As ₄	α_2	Y	1a
16	WGe ₂ As ₄	α_2	Y	1a
17	WSn ₂ N ₄	α_1	Y	1a
18	MoS ₂	2H	Y	1c,1e
19	InSe	α	Y	1a,1c

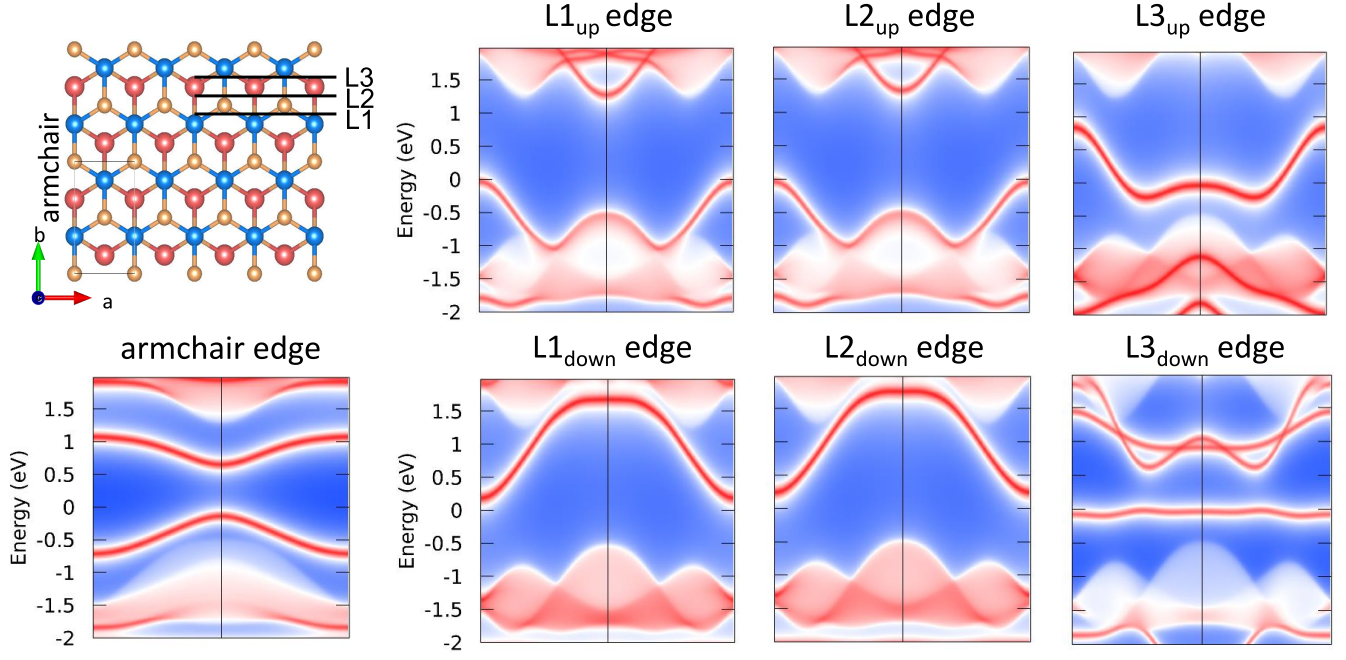


FIG. A3. (color online) The top left panel is the top view of MoSi₂N₄ monolayer. There are seven types of edges. Armchair edge is clear shown in figure. Another six edges, L_{iup} and L_{idown} ($i=1, 2, 3$) edge, are obtained by three cutting lines, where subscript up and down are the edge above or below line L_i . The projected edge states for L_{iup} and L_{idown} ($i=1, 2, 3$) and armchair edges are shown in another six panels.

TABLE A4. The structural information about nine C₃-symmetric nanodisks, where center type "2N" means two N atoms at the center of nanodisk and "2Si 2N" means two N atom and two Si atoms at the center of nanodisk; N_{Mo} , N_{Si} , and N_N are the number of atoms of Mo, Si, and N in nanodisk; SR is the stoichiometric ratio in nanodisk, normalized down to N atoms.

No.	C_n	shape	edge type	center type	N_{Mo}	N_{Si}	N_N	SR
01	C ₃	hexagonal	armchair	2N	42	84	170	1.00:2.00:4.05
02	C ₃	hexagonal	armchair	2Si 2N	42	86	170	1.00:2.05:4.05
03	C ₃	hexagonal	armchair	1Mo	43	84	168	1.00:1.95:3.91
04	C ₃	triangle	armchair	2N	30	60	122	1.00:2.00:4.07
05	C ₃	triangle	armchair	2Si 2N	30	62	122	1.00:2.07:4.07
06	C ₃	triangle	armchair	1Mo	31	60	120	1.00:1.94:3.87
07	C ₃	triangle	L2 _{down}	2N	15	42	98	1.00:2.80:6.53
08	C ₃	triangle	L1 _{down}	2Si 2N	21	56	86	1.00:2.67:4.10
09	C ₃	triangle	L3 _{down}	1Mo	28	30	72	1.00:1.07:2.57

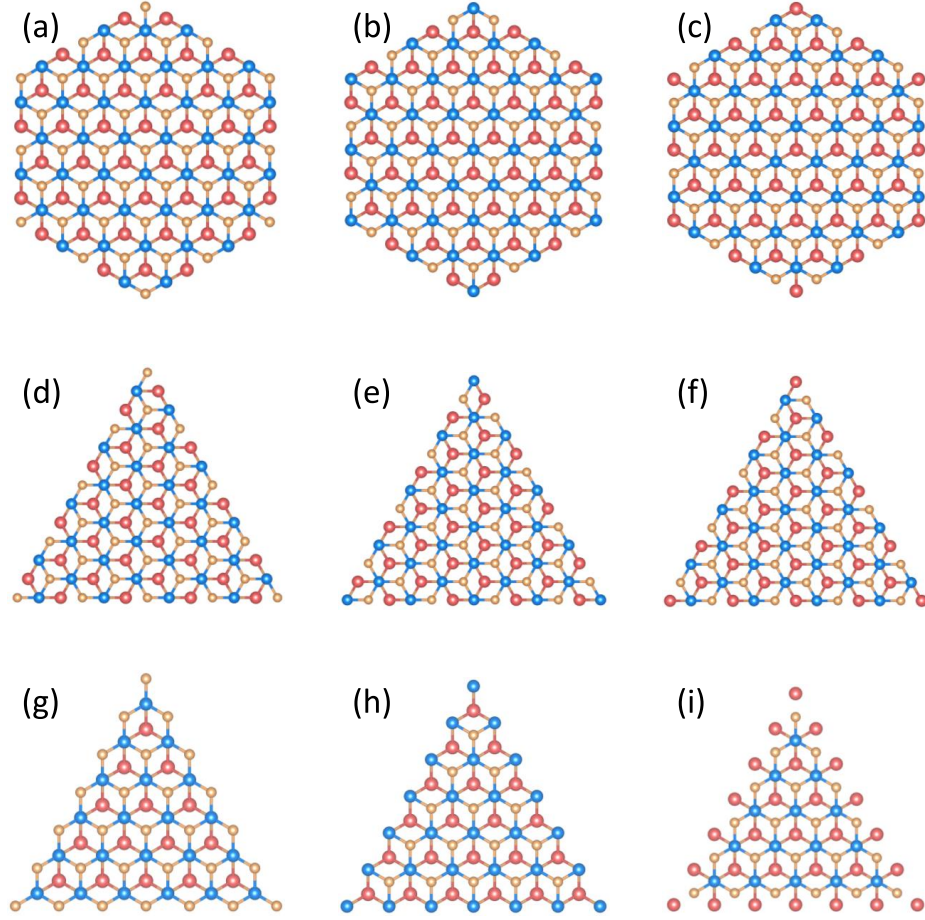


FIG. A4. (color online) Hexagonal and triangle C_3 -symmetric nanodisk with armchair, and Li_{down} ($i = 1, 2, 3$) edge, corresponding to **Table A4**.

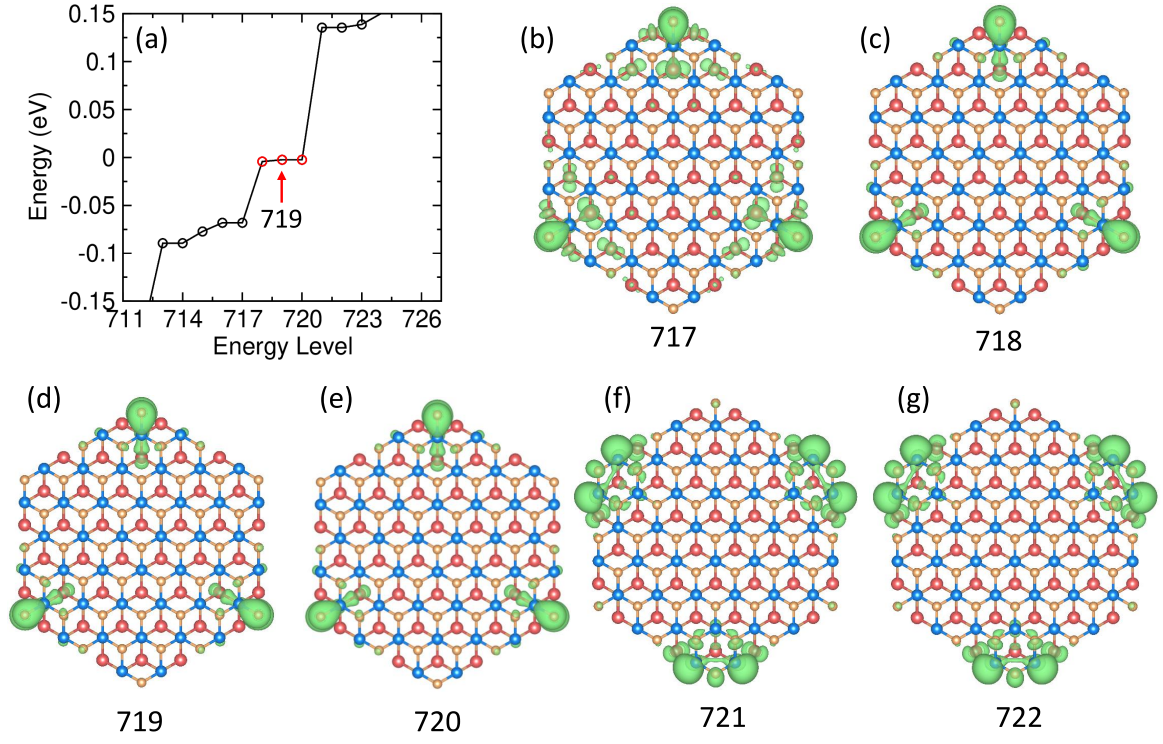


FIG. A5. (color online) (a) The energy spectrum of C_3 -symmetric N-centered hexagonal nanodisk of MoSi_2N_4 . Where red circles is corner states. (b-g) show the charge distribution of its corresponding energy level.

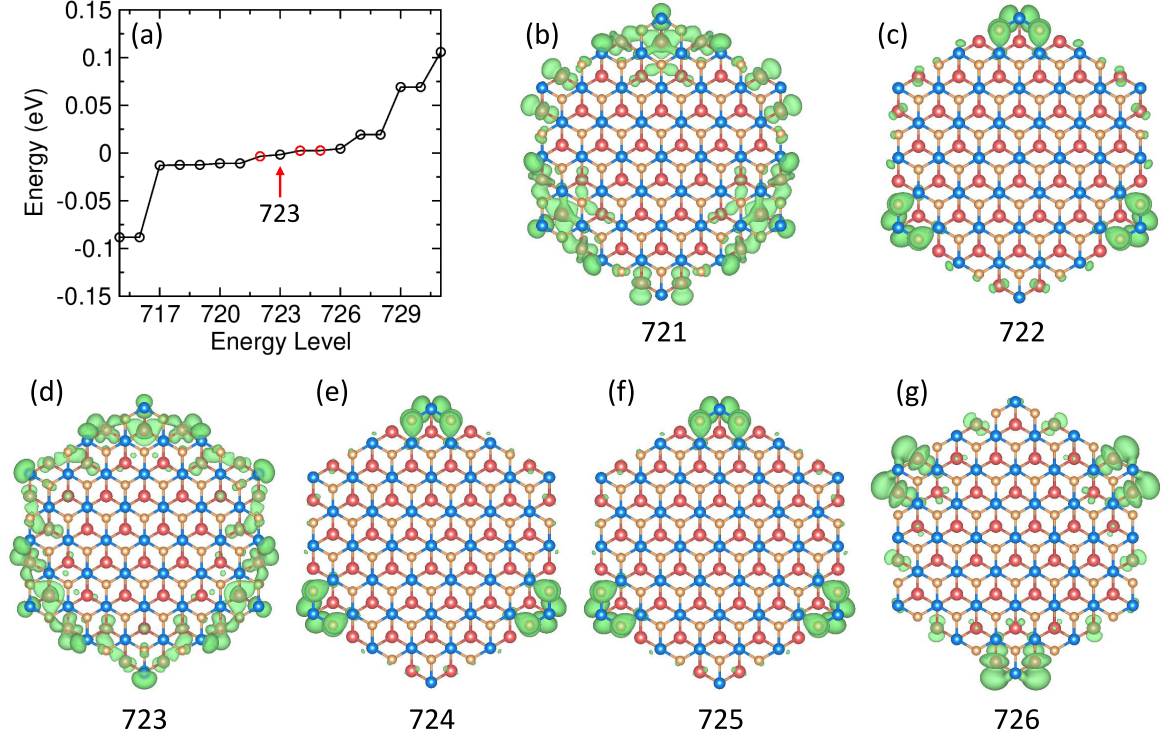


FIG. A6. (color online) (a) The energy spectrum of C_3 -symmetric Si-centered hexagonal nanodisk of MoSi_2N_4 . Where red circles is corner states. (b-g) show the charge distribution of its corresponding energy level.

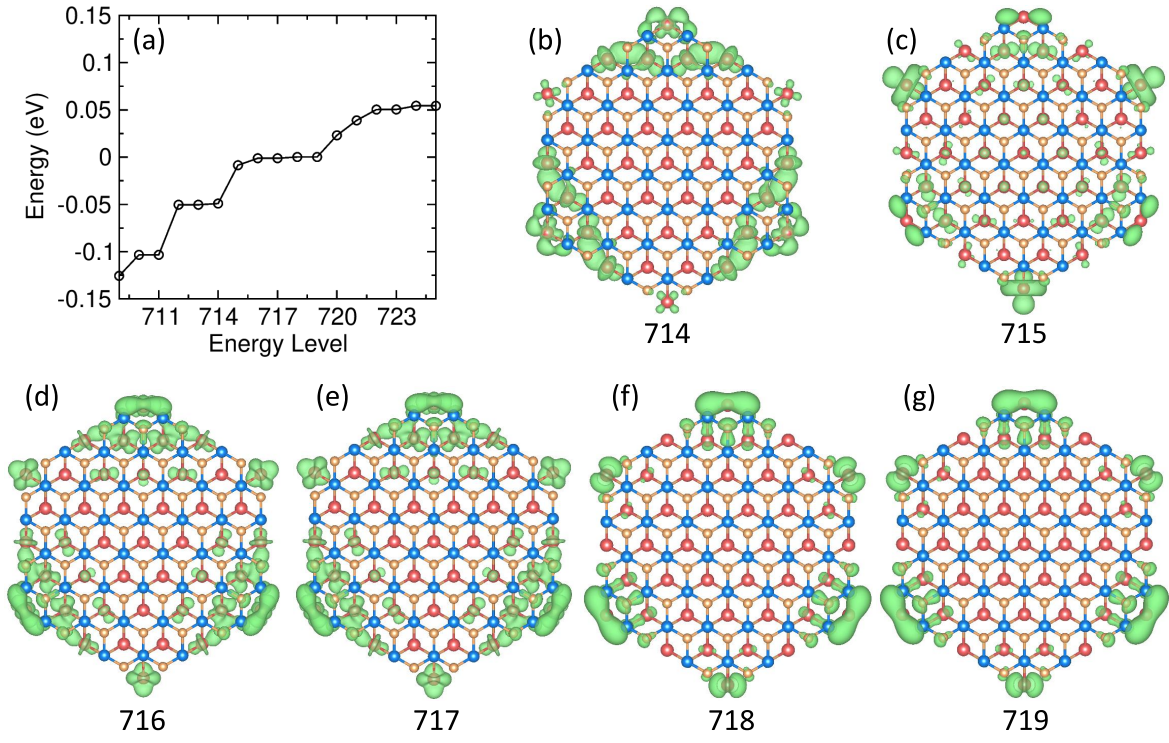


FIG. A7. (color online) (a) The energy spectrum of C_3 -symmetric Mo-centered hexagonal nanodisk of MoSi_2N_4 . (b-g) show the charge distribution of its corresponding energy level.